MPS6717

One Watt Amplifier Transistor

NPN Silicon

Features

Pb–Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	80	Vdc
Collector-Base Voltage	V _{CBO}	80	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current – Continuous	Ι _C	500	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	1.0 8.0	W mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	2.5 20	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

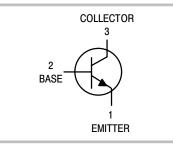
Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	50	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



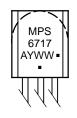
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



MPS6717 = Device Code А

= Assembly Location

= Year

Y

WW

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MPS6717	TO-92	5000 Units / Bulk
MPS6717G	TO-92 (Pb-Free)	5000 Units / Bulk
MPS6717RLRA	TO-92	2000/Tape & Reel
MPS6717RLRAG	TO-92 (Pb-Free)	2000/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

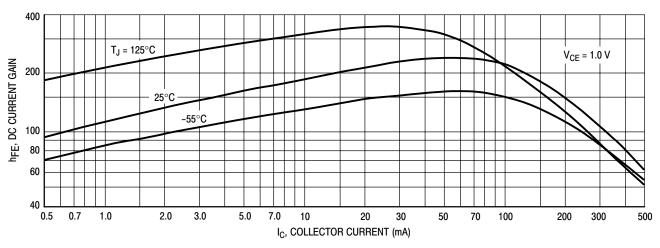
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MPS6717

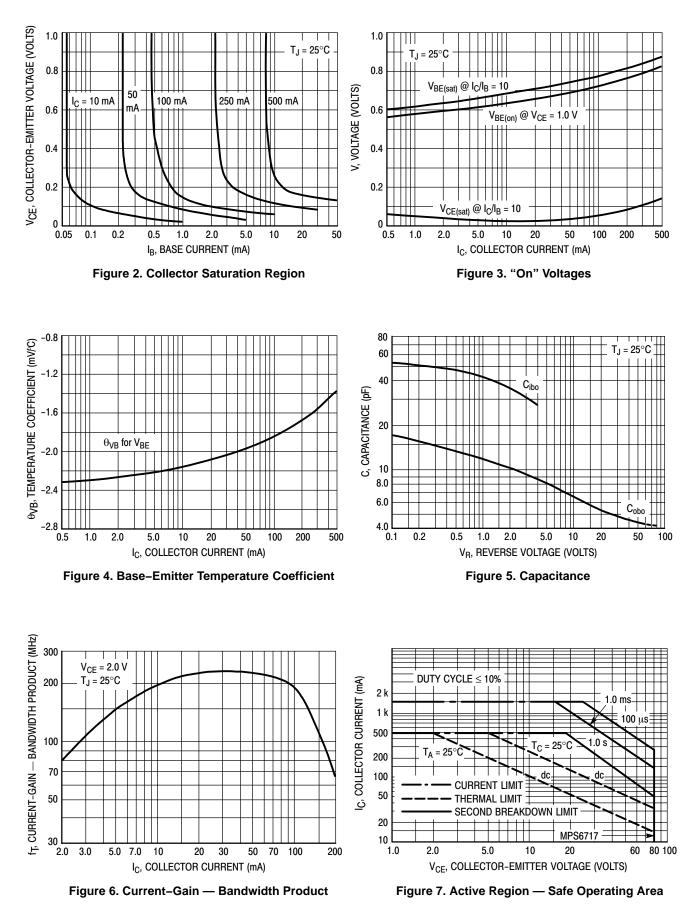
ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	·			
Collector – Emitter Breakdown Voltage (Note 1) ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	80	_	Vdc
Collector – Base Breakdown Voltage ($I_C = 100 \ \mu Adc, I_E = 0$)	V _{(BR)CBO}	80	_	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \ \mu Adc, I_C = 0$)	V _{(BR)EBO}	5.0	_	Vdc
Collector Cutoff Current ($V_{CB} = 60$ Vdc, $I_E = 0$)	I _{CBO}	-	0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 5.0 \text{ Vdc}, I_C = 0$)	I _{EBO}	-	10	μAdc
ON CHARACTERISTICS		•		
DC Current Gain (I _C = 50 mAdc, V _{CE} = 1.0 Vdc) (I _C = 250 mAdc, V _{CE} = 1.0 Vdc)	h _{FE}	80 50	250	-
Collector – Emitter Saturation Voltage $(I_C = 250 \text{ mAdc}, I_B = 10 \text{ mAdc})$	V _{CE(sat)}	-	0.5	Vdc
Base-Emitter On Voltage (I _C = 250 mAdc, V _{CE} = 1.0 Vdc)	V _{BE(on)}	_	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Collector–Base Capacitance $(V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C _{cb}	-	30	pF
Small–Signal Current Gain (I _C = 200 mAdc, V _{CE} = 5.0 Vdc, f = 20 MHz)	h _{fe}	2.5	25	-

1. Pulse Test: Pulse Width \leq 300 µs; Duty Cycle \leq 2.0%.

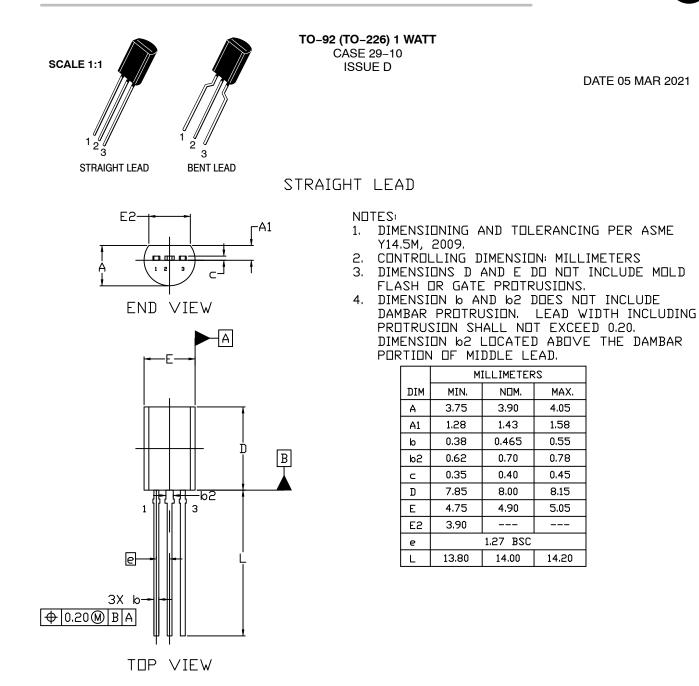






MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS





STYLES AND MARKING ON PAGE 3

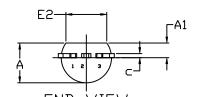
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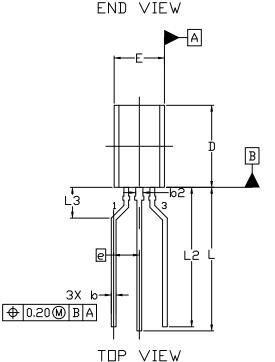


TO-92 (TO-226) 1 WATT CASE 29–10 ISSUE D

DATE 05 MAR 2021

FORMED LEAD





NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS,
- 4. DIMENSION ७ AND ७2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION ७2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS			
DIM	MIN.	NDM.	MAX.	
Α	3.75	3.90	4.05	
A1	1.28	1.43	1.58	
σ	0.38	0.465	0.55	
b2	0.62	0.70	0.78	
с	0.35	0.40	0.45	
D	7.85	8.00	8.15	
Е	4.75	4.90	5.05	
E2	3.90			
e	2.50 BSC			
L	13.80	14.00	14.20	
L2	13.20	13.60	14.00	
L3	3.00 REF			

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DATE 05 MAR 2021

	EMITTER BASE COLLECTOR
	GATE SOURCE & SUBSTRATE DRAIN
2.	ANODE CATHODE & ANODE CATHODE
2.	ANODE GATE CATHODE
2.	COLLECTOR EMITTER BASE

STYLE 2: PIN 1. BASE 2. EMITTER 3. COLLECTOR STYLE 7: PIN 1. SOURCE 2. DRAIN 3. GATE STYLE 12: PIN 1. MAIN TERMINAL 1 2. GATE 3. MAIN TERMINAL 2 STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER STYLE 22: PIN 1. SOURCE 2. GATE 3. DRAIN STYLE 27: PIN 1. MT 2. SUBSTRATE 3. MT STYLE 32 PIN 1. BASE 2. COLLECTOR 3. EMITTER

style Pin	1. 2.	ANODE ANODE CATHODE
Style Pin	1. 2.	DRAIN GATE SOURCE & SUBSTRATE
Style Pin	1. 2.	ANODE 1 GATE CATHODE 2
style Pin	1. 2.	ANODE CATHODE NOT CONNECTED
style Pin	1. 2.	GATE SOURCE DRAIN
style Pin	1. 2.	CATHODE ANODE GATE
style Pin	1. 2.	RETURN INPUT OUTPUT

STYLE 4: PIN 1. CATHODE STYLE 5: 2. CATHODE 3. ANODE STYLE 9: PIN 1. BASE 1 2. EMITTER 3. BASE 2 STYLE 14: PIN 1. EMITTER 2. COLLECTOR 3. BASE STYLE 19: PIN 1. GATE 2. ANODE 3. CATHODE STYLE 24: PIN 1. EMITTER 2. COLLECTOR/ANODE 3. CATHODE STYLE 29: PIN 1. NOT CONNECTED 2. ANODE 3. CATHODE STYLE 34: PIN 1. INPUT

2. GROUND 3. LOGIC

PIN 1. DRAIN 2. SOURCE 3. GATE STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2 STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE STYLE 35: PIN 1. GATE 2. COLLECTOR 3. EMITTER

GENERIC MARKING DIAGRAM*

XXXXX XXXXX ALYW

XXXX = Specific Device Code

- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
 - = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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